

NPN Triple Diffused Planar Type Silicon Transistor

**2SC3461**



**800V/8A Switching Regulator Applications**

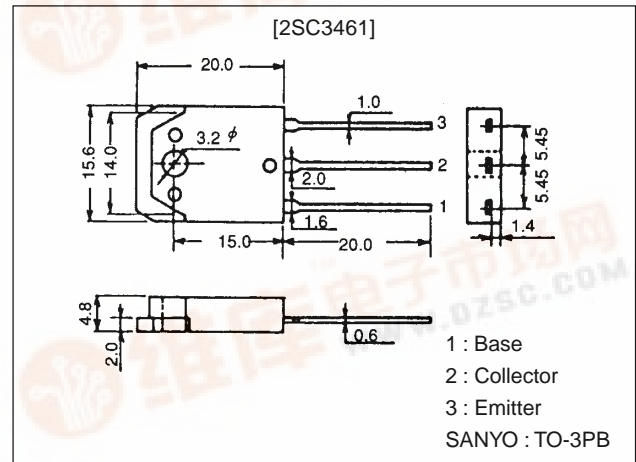
**Features**

- High breakdown voltage and high reliability.
- Fast switching speed ( $t_f$ : 0.1 $\mu$ s typ).
- Wide ASO.
- Adoption of MBIT process.

**Package Dimensions**

unit:mm

2022A



**Specifications**

**Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	$V_{CB0}$		1100	V
Collector-to-Emitter Voltage	$V_{CEO}$		800	V
Emitter-to-Base Voltage	$V_{EBO}$		7	V
Collector Current	$I_C$		8	A
Collector Current (Pulse)	$I_{CP}$	$PW \leq 300\mu s$ , Duty Cycle $\leq 10\%$	25	A
Base Current	$I_B$		4	A
Collector Dissipation	$P_C$	$T_c = 25^\circ C$	140	W
Junction Temperature	$T_j$		150	$^\circ C$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ C$

**Electrical Characteristics at Ta = 25°C**

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 800V$ , $I_E = 0$			10	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5V$ , $I_C = 0$			10	$\mu A$
DC Current Gain	$h_{FE1}$	$V_{CE} = 5V$ , $I_C = 0.6A$	10*		40*	
	$h_{FE2}$	$V_{CE} = 5V$ , $I_C = 3A$	8			
Gain-Bandwidth Product	$f_T$	$V_{CE} = 10V$ , $I_C = 0.6A$		15		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10V$ , $f = 1MHz$		155		pF

\* : The  $h_{FE1}$  of the 2SC3461 is classified as follows. When specifying the  $h_{FE1}$  rank, specify two ranks or more in principle.

10	K	20	15	L	30	20	M	40
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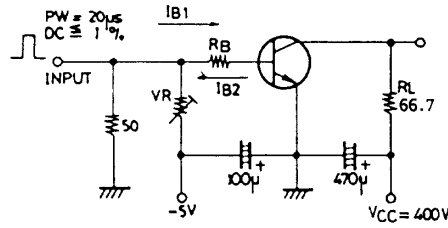
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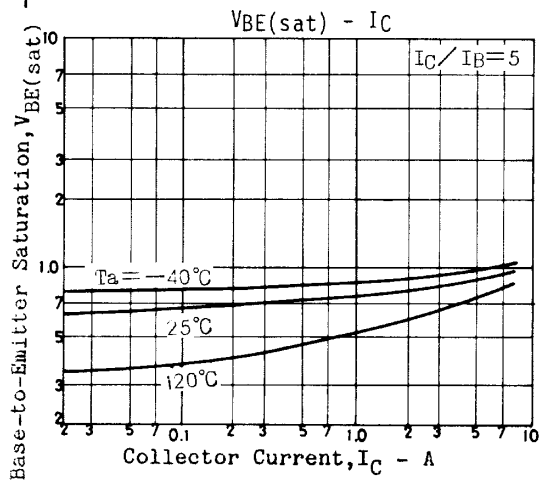
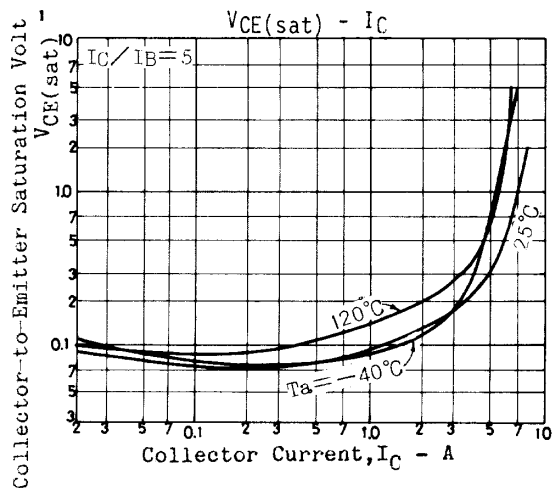
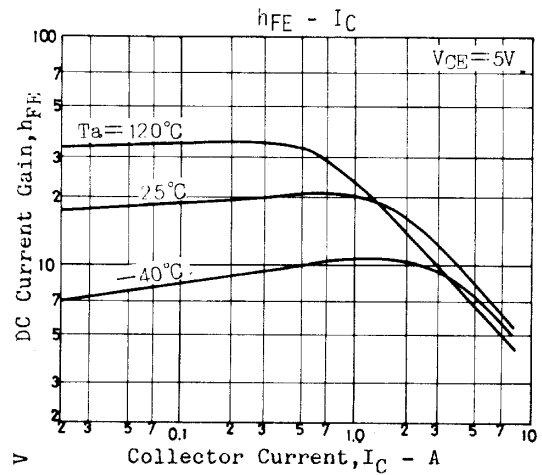
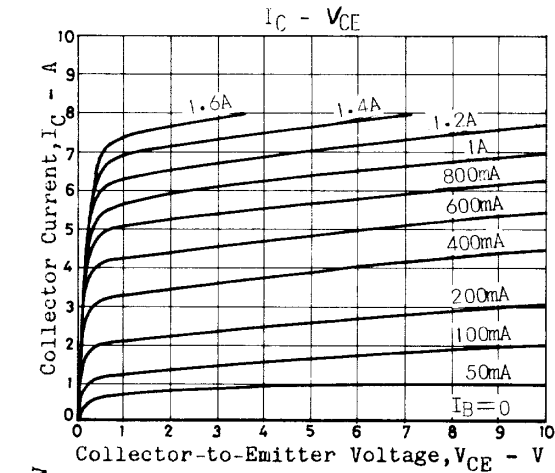
## 2SC3461

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4A, I_B=0.8A$			2.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=4A, I_B=0.8A$			1.5	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	1100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	800			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V
Collector-to-Emitter Sustain Voltage	$V_{CEX(sus)}$	$I_C=4A, 2I_{B1}=-I_{B2}=0.8A, L=1mH, \text{clamped}$	800			V
Turn-ON Time	$t_{on}$	$V_{CC}=400V, 5I_{B1}=-2.5I_{B2}=I_C=6A, R_L=66.7\Omega$			0.5	$\mu s$
Storage Time	$t_{stg}$	$V_{CC}=400V, 5I_{B1}=-2.5I_{B2}=I_C=6A, R_L=66.7\Omega$			3.0	$\mu s$
Fall Time	$t_f$	$V_{CC}=400V, 5I_{B1}=-2.5I_{B2}=I_C=6A, R_L=66.7\Omega$			0.3	$\mu s$

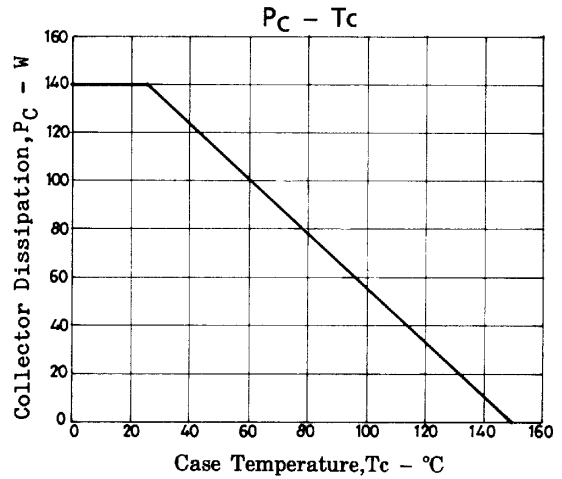
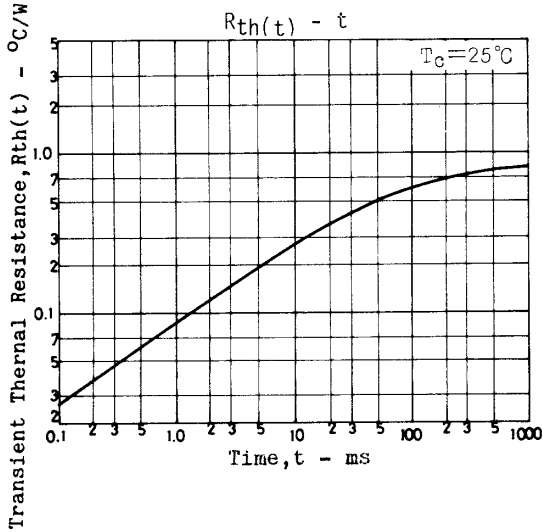
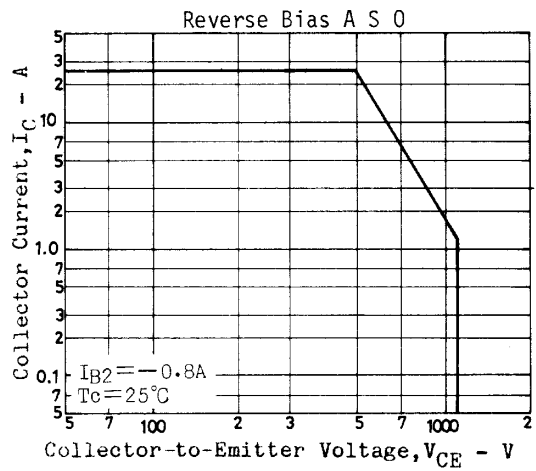
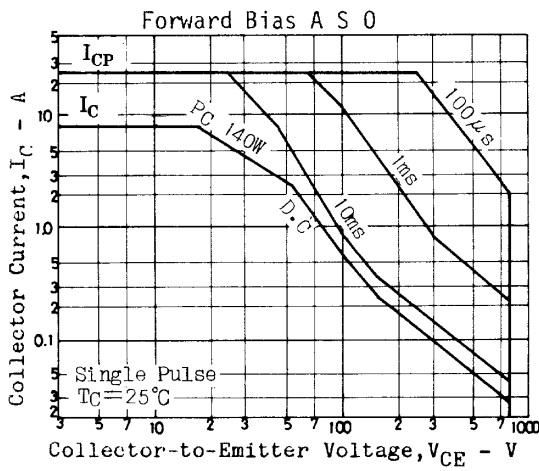
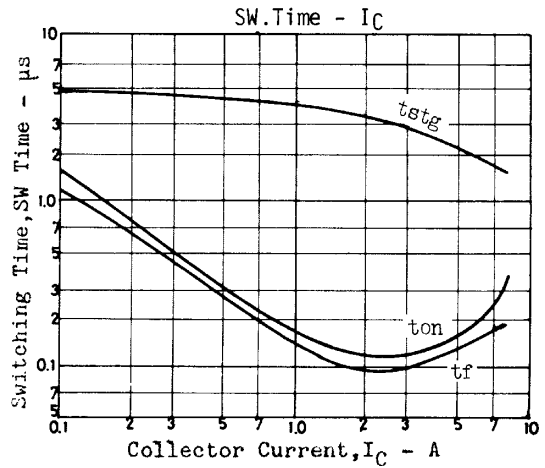
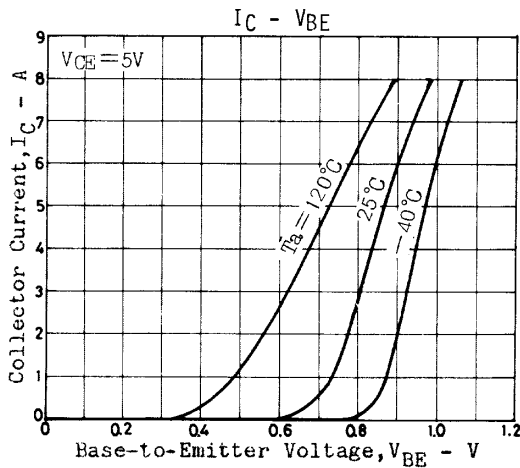
### Switching Time Test Circuit



Unit (resistance :  $\Omega$ , capacitance : F)



# 2SC3461



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